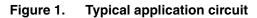
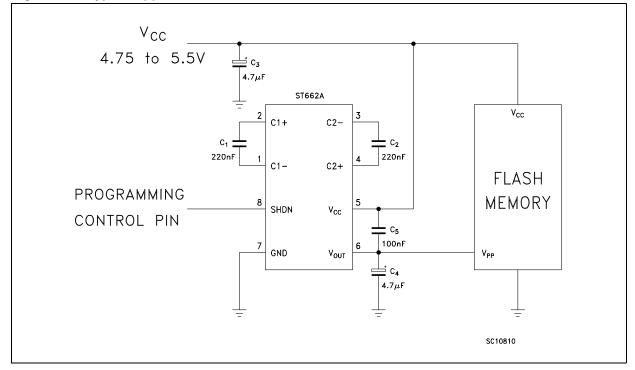
## Contents

1	Application circuit
2	Pin configuration
3	Maximum ratings 5
4	Electrical characteristics
5	Typical performance characteristics7
6	Description
7	Application circuit         11           7.1         ST662A output performance         12
8	How to increase output current or output voltage capability 14
9	Package mechanical data 16
10	Revision history



## 1 Application circuit







## 2 Pin configuration

Figure 2. Pin connections (top view)

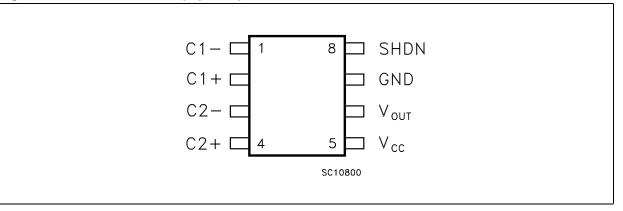


Table 2.Pin description

Pin n°	Symbol	Name and function
1	C1-	Negative terminal for the first charge pump capacitor
2	C1+	Positive terminal for the first charge pump capacitor
3	C2-	Negative terminal for the second charge pump capacitor
4	C2+	Positive terminal for the second charge pump capacitor
5	V <sub>CC</sub>	Supply voltage
6	V <sub>OUT</sub>	12 V output voltage $V_{OUT} = V_{CC}$ when in shutdown mode
7	GND	Ground
8	SHDN	Active high C-MOS logic level shutdown input. SHDN is internally pulled up to V <sub>CC</sub> . Connect to GND for normal operation. In Shutdown mode the charge pumps are turned off and V <sub>OUT</sub> = V <sub>CC</sub>





## 3 Maximum ratings

Table 3.	Absolute maximum ratings	
----------	--------------------------	--

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC input voltage to GND	-0.3 to 6	V	
SHDN	Shutdown voltage	-0.3 to (V <sub>CC</sub> + 0.3)	V	
۱ <sub>0</sub>	Output current continuous	50	A	
PD	Power dissipation		500	mW
т		AC series	0 to 70	°C
T <sub>OP</sub>	Operating ambient temperature range AB series		-40 to 85	
T <sub>STG</sub>	Storage temperature range		-40 to 150	°C

Note: Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

#### Table 4.Thermal data

Symbol	Parameter	SO-8	Unit
R <sub>thJC</sub>	Thermal resistance junction-case	20	°C/W



## 4 Electrical characteristics

Refer to the test circuits, V<sub>CC</sub> = 4.5 V to 5.5 V, T<sub>A</sub> = T<sub>MIN</sub> to T<sub>MAX</sub>, unless otherwise specified. Typical value are referred at T<sub>A</sub> = 25 °C.

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
V	Output voltage	I <sub>O</sub> = 0 to 20 mA	11.4	12	12.6	V	
Vo	Output voltage	$I_{O}$ = 0 to 30 mA, $V_{CC}$ = 4.75 to 5.5 V	11.4	12	12.6	v	
I <sub>Q1</sub>	Quiescent current	NO LOAD, V <sub>SHDN</sub> = 0		100	500	μA	
I <sub>Q2</sub>	Shutdown current	NO LOAD, V <sub>SHDN</sub> = V <sub>CC</sub>		1	10	μA	
	Shutdown pin current	$V_{SHDN} = 0, V_{CC} = 5V$	-50	-12	-5	μA	
I <sub>SH</sub>	Shutdown pin current	$V_{SHDN} = V_{CC} = 5V$		0		μA	
V <sub>IL</sub>	Shutdown input low threshold				0.4	V	
V <sub>IH</sub>	Shutdown input high threshold		2.4			V	
f <sub>O</sub>	Oscillator frequency	$V_{CC} = 5 \text{ V}, \text{ I}_{O} = 30 \text{ mA}$		400		kHz	
n	Power efficiency	$V_{CC} = 5 \text{ V}, \text{ I}_{O} = 30 \text{ mA}$		72		%	
$R_{SW}$	$V_{CC}$ - $V_{OUT}$ switch impedance	$V_{SHDN} = V_{CC} = 5V$ , $I_O = 100 \ \mu A$		1	2	kΩ	

 Table 5.
 Electrical characteristics

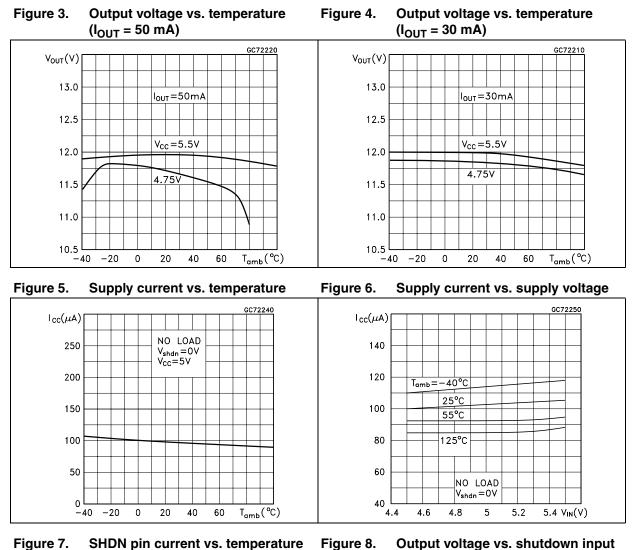
Refer to the test circuits, V<sub>CC</sub> = 4.5 V to 5.5 V, T<sub>A</sub> = -40 to 125 °C, unless otherwise specified. Typical value are referred at T<sub>A</sub> = 25 °C.

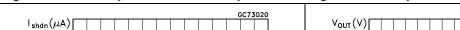
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V.	Output voltage	I <sub>O</sub> = 0 to 20 mA	11.2	12	12.8	V
Vo	Ouiput voltage	$I_{O} = 0$ to 30 mA, $V_{CC} = 4.75$ to 5.5 V	11.2	12	12.8	v
I <sub>Q1</sub>	Quiescent current	NO LOAD, V <sub>SHDN</sub> = 0		100	500	μA
I <sub>Q2</sub>	Shutdown current	NO LOAD, $V_{SHDN} = V_{CC}$		1	15	μA
	I <sub>SH</sub> Shutdown pin current	$V_{SHDN} = 0, V_{CC} = 5V$	-50	-12	-5	μA
I <sub>SH</sub>	Shutdown pin current	$V_{SHDN} = V_{CC} = 5V, T_A = 25^{\circ}C$		0		μA
V <sub>IL</sub>	Shutdown input low threshold				0.4	V
V <sub>IH</sub>	Shutdown input high threshold		2.4			V
f <sub>O</sub>	Oscillator frequency	$V_{CC} = 5 \text{ V}, \text{ I}_{O} = 30 \text{ mA}, \text{ T}_{A} = 25^{\circ}\text{C}$		400		kHz
n	Power efficiency	$V_{CC} = 5 \text{ V}, \text{ I}_{O} = 30 \text{ mA}, \text{ T}_{A} = 25^{\circ}\text{C}$		72		%
R <sub>SW</sub>	V <sub>CC</sub> - V <sub>OUT</sub> switch impedance	$V_{SHDN} = V_{CC} = 5V$ , $I_O = 100 \ \mu A$		1	2	kΩ

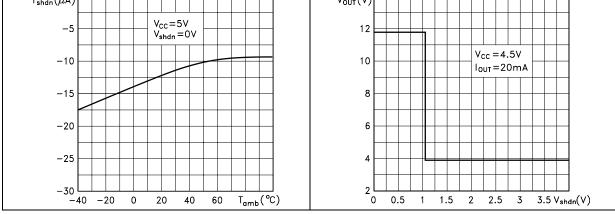
#### Table 6. Electrical characteristics for ST662AB-TRY (Automotive Grade)



## 5 Typical performance characteristics

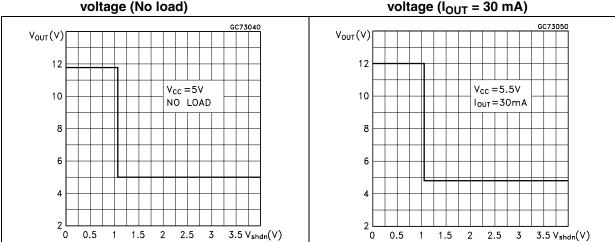






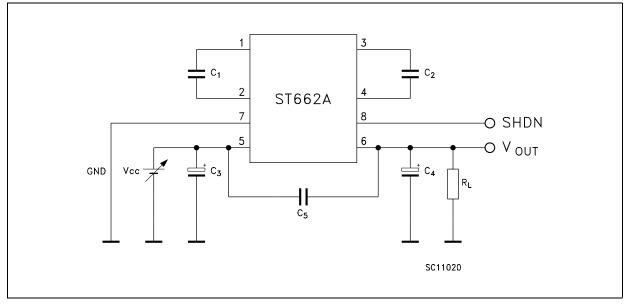
Doc ID 5068 Rev 8

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# Figure 9. Output voltage vs. shutdown input Figure 10. Output voltage vs. shutdown input voltage (No load) voltage (I<sub>OUT</sub> = 30 mA)

#### Figure 11. Test circuit



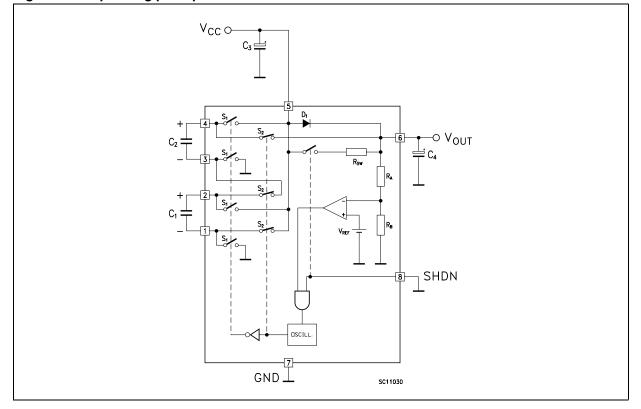


#### 6 Description

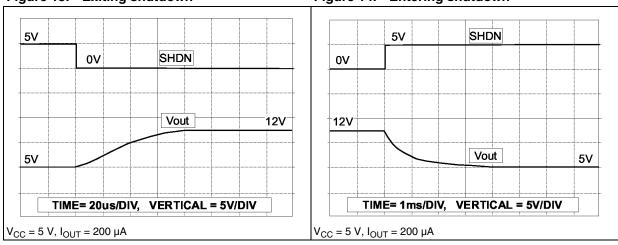
The ST662 is an IC developed to provide a 12 V regulated output 30 mA from voltage input as low as 4.75 without any inductors. It is useful for a wide range of applications and its performances make it ideal for Flash memory programming supply.

An evaluation kit is provided to facilitate the application. This include a single-side demo board designed for surface-mount components. The operating principle of ST662 (see *Figure 12*) is to charge C1 and C2 capacitor by closing the S1 switch (while S2 is opened) at the V<sub>CC</sub> voltage. After S1 is opened and S2 closed so that C1 and C2 capacitors are placed in series one to each other, and both are in series with V<sub>IN</sub>. The sum of V<sub>C1</sub> and V<sub>C2</sub> and V<sub>I</sub> is applied to the capacitor C4. This works as voltage triple. An amplifier error checks the output voltage and blocks the oscillator if the output voltage is greater than 12 V. The shutdown pin is internally pulled to V<sub>CC</sub>. When it is held low the output voltage rises to +12 V. *Figure 13* shows the transition time of the shut down pin when the V<sub>SHDN</sub> goes from 5 V to 0 V. Input logic levels of this input are CMOS compatible Applying a logic high at this input, the V<sub>OUT</sub> oscillator is blocked and the V<sub>OUT</sub> is reach the V<sub>I</sub> value by D1. In this condition I<sub>CC</sub> is low as 1 µA. The *Figure 14* shows the transition time of the shut down pin when the V<sub>SHDN</sub> goes from 0 V to 5 V.

Figure 12. Operating principle circuit







#### Figure 13. Exiting shutdown Figure 14. Entering shutdown

10/20



## 7 Application circuit

Based on fast charge/discharge of capacitors, this circuit involves high di/dt values limited only by  $R_{ON}$  of switches. This implies a critical layout design due to the need to minimize inductive paths and place capacitors as close as possible to the device.

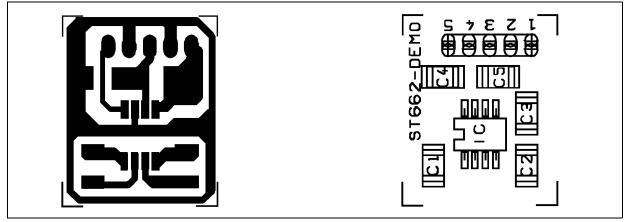
A good layout design is strongly recommended for noise reason. For best performance, use very short connections to the capacitors and the values shown in *Table 7*.

C3 and C4 must have low ESR in order to minimize the output ripple. Their values can be reduced to 2  $\mu$ F and 1  $\mu$ F, respectively, when using ceramic capacitors, but must be of 10  $\mu$ F or larger if aluminium electrolytic are chosen.

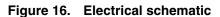
C5 must be placed as close to the device as possible and could be omitted if very low output noise performance are not required.

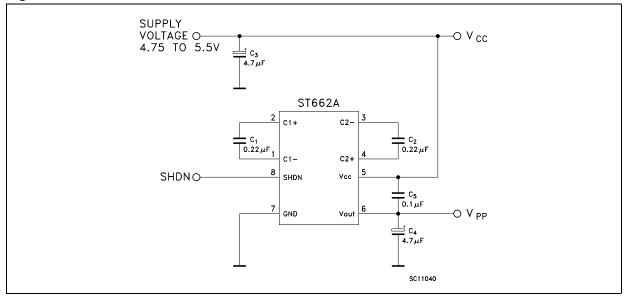
Figure 15 and Figure 16 show, respectively, our EVALUATION kit layout and the relatively.

Figure 15. KIT layout







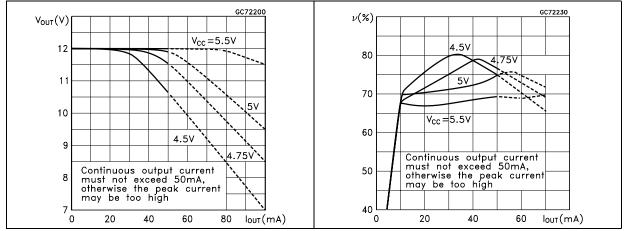


#### Table 7. List of component

Capacitor	Туре	Value (µF)
Charge pump C1	Ceramic	0.22
Charge pump C1	Ceramic	0.22
Input C3	Electrolytic tantalum	4.7
Output C4	Electrolytic tantalum	4.7
Decoupling C5	Ceramic	0.1

#### 7.1 ST662A output performance





Doc ID 5068 Rev 8



-lout-

Vout 100mV/div

 $V_{CC} = 5 \text{ V}, \text{ I}_{OUT} = 0 \text{ to } 30\text{mA}$ 

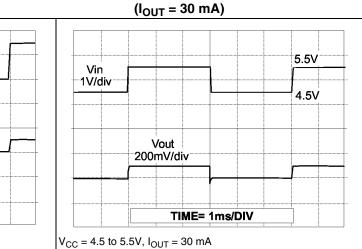
20mA/div

# Figure 19. Load transient response (I<sub>OUT</sub> = 0 to 30 mA)

SHDN

Vout

TIME= 1ms/DIV



## Figure 20. Load transient response $(l_{aver} = 30 \text{ mA})$

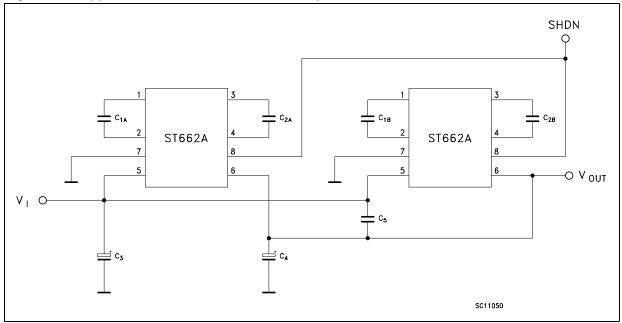


# 8 How to increase output current or output voltage capability

Current capability is limited by R<sub>ON</sub> of internal switches. It is possible to increase it connecting in parallel two or more ST662A devices; each one of them can supply 30 mA. The *Figure 19* shows the electric schematic. The capacitors C3, C4 and C5 must be placed very close to the ICs on the board. If this is not possible, you can place two different capacitors, each of them of half value, very close to the respective integrated circuit.

Figure 23 show the output current capability of the proposed circuit.

If an output voltage greater than 12 V is required, it's possible to realize the circuit of the following diagram *Figure 22*. The relevant output current capability is shown in *Figure 24* in which is shown the output voltage vs. load current.



#### Figure 21. Application circuit for two ST662A in parallel

Table 8.	List of component

Capacitor	Туре	Value (µF)
C1A	Ceramic	0.22
C2A	Ceramic	0.22
C1B	Ceramic	0.22
C2B	Ceramic	0.22
C3	Electrolytic Tantalum	10
C4	Electrolytic Tantalum	10
C5	Ceramic	0.22



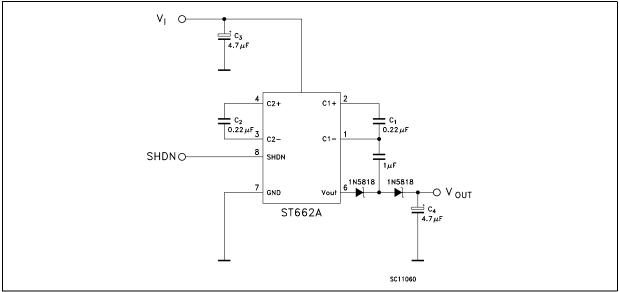
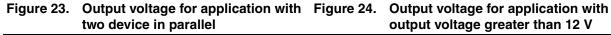
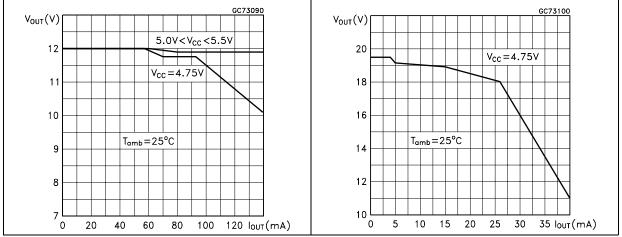


Figure 22. Application circuit for output voltage greater than 12 V







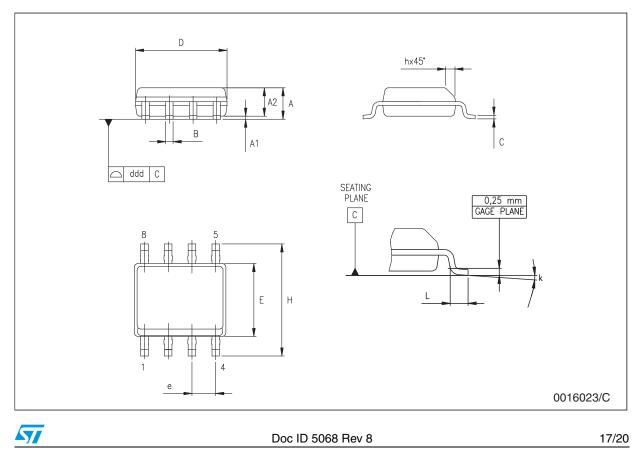
## 9 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

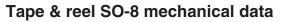
16/20

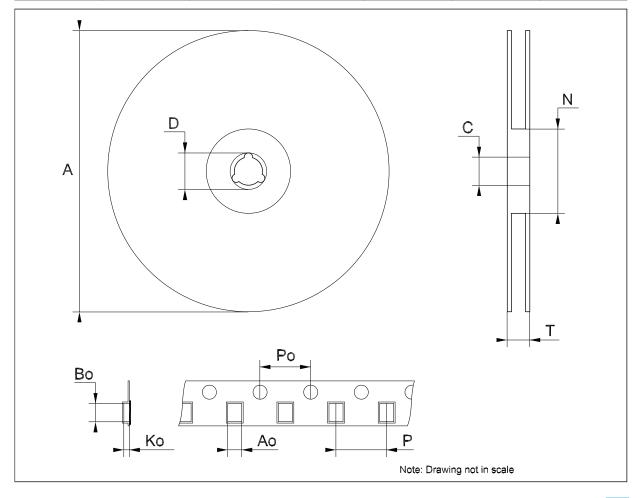


Typ.	Max.           1.75           0.25           1.65           0.51	Min.           0.053           0.04           0.043	Тур.	Max. 0.069 0.010 0.065
	0.25	0.04		0.010
	1.65	0.043		
				0.065
	0.51	0.010		1
		0.013		0.020
	0.25	0.007		0.010
	5.00	0.189		0.197
	4.00	0.150		0.157
1.27			0.050	
	6.20	0.228		0.244
	0.50	0.010		0.020
	1.27	0.016		0.050
	8° (	max.)		
	1.27	4.00       1.27       6.20       0.50       1.27	4.00       0.150         1.27       6.20       0.228         0.50       0.010       1.27         1.27       0.016       8° (max.)	4.00       0.150         1.27       0.050         6.20       0.228         0.50       0.010         1.27       0.016         8° (max.)



Dim.		mm.			inch.		
Dini.	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			330			12.992	
С	12.8		13.2	0.504		0.519	
D	20.2			0.795			
Ν	60			2.362			
Т			22.4			0.882	
Ao	8.1		8.5	0.319		0.335	
Bo	5.5		5.9	0.216		0.232	
Ko	2.1		2.3	0.082		0.090	
Po	3.9		4.1	0.153		0.161	
Р	7.9		8.1	0.311		0.319	





Doc ID 5068 Rev 8



18/20

# 10 Revision history

Date	Revision	Changes
16-Jul-2007	5	Device summary updated.
07-Feb-2008	6	Modified: Table 1 on page 1.
19-Feb-2008	7	Add new order code for Automotive grade products see Table 1 on page 1.
03-Aug-2010	8	Modified <i>Features on page 1</i> .

#### Table 9.Document revision history



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20/20

Doc ID 5068 Rev 8

